

WeEn Semiconductors Application Note

WAN012

PD Charger (120W) Reference Design

1. Introduction

Power delivery (PD) chargers are a much faster, smarter and safer way to charge devices such as laptops, phones, battery packs etc. This WAN012 Application Note describes a reference design for a 120W PD fast charger with PFC + LLC topology which uses a WeEn Semiconductors silicon carbide (SiC) rectifier diode in the PFC stage.

Silicon carbide (SiC) is a third-generation wide-bandgap semiconductor material which has greater dielectric breakdown strength, faster saturated electron drift speed and higher thermal conductivity compared to silicon material (Si). Consequently, a SiC power device can help reduce energy consumption and system size for power converter designs. Presently, SiC devices are widely used in electric vehicles, inverters, railway systems and solar and wind power generation systems. With the emerging technology of high-power PD fast chargers, SiC diodes have also begun to emerge in consumer PD chargers with peak charging power over 100W.

For the PFC stage a 6A, 650V, WeEn Semiconductors SiC diode is used as the rectifier diode. The SiC diode brings several advantages for the charger system which include reduced thermal stress, improved power efficiency and improved EMI performance. Figure 1 shows the PCB assembly of the PD fast charger.



Demo board	Description	SiC Diode
PDC120W	120W PFC+LLC Topology	WNSC2D06650D

Fig. 1. PD fast charger PCB

2. PD Charger using SiC diode

In order to increase the power factor of high-power power products and reduce the interference and pollution of harmonics to the grid, 3C certification (China National Compulsory Product Certification) requires active PFC circuits for a charging source above 75W.

A commonly used active PFC circuit is shown in Figure 2.

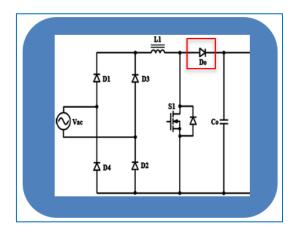


Fig. 2 Typical PFC boost circuit

The choice of the SiC diode as the rectification diode in the PFC compared with a traditional Si diode in this application has several advantages:-

• The SiC diode has nearly zero reverse recovery current compared to that of a Si diode and so power losses are reduced as well as heat generation. (See Figure. 3 and Figure. 4)

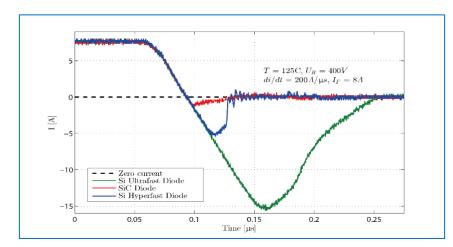


Fig. 3. Graphic showing the nearly zero reverse recovery current of SiC diode (red trace)

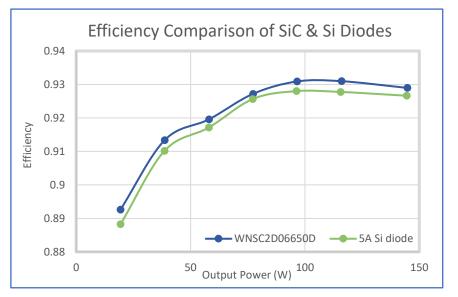


Fig. 4. Graphic showing improved power efficiency of converter using SiC diode

• SiC material has better thermal conductivity, which is beneficial for heat transfer and consequently a reduced junction temperature during operation. This also improves reliability. (See Figure. 5)

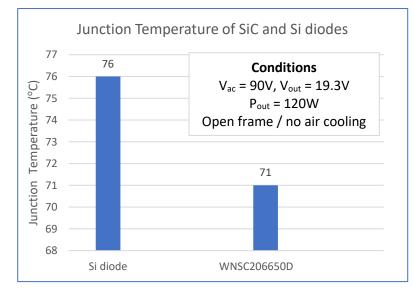


Fig. 5. Graphic showing reduced power efficiency of converter using SiC diode

- The switching or operating frequency can be increased to 300KHz from a usual frequency of less than 100KHz. This means the size of the boost inductor and consequently the size of the charger can be reduced to achieve a higher power density at reduced overall cost.
- A smaller reverse recovery current gives WNSC206650D better EMI performance and helps to achieve the Class B requirements in the GB/IEC Standard.

All information provided in this document is subject to legal disclaimers.

3. WeEn SMD SiC diodes

WeEn Semiconductor has surface mount packages (SMDs) dedicated for fast PD charger design. Currently available packages include DPAK and DFN. These packages have particular features which benefit users:-

- Very low thermal impedance. The WeEn SiC SMD diode uses a silver sintered chip soldering process. This yields a low thermal impedance which enhances heat dissipation and helps maintain a low junction temperature.
- Leadless package DFN 8x8. The leadless package reduces parasitic inductance and resistance and therefore is suitable for higher frequency operation. It has a low package profile with a total thickness for the DFN package of less than 1mm. This facilitates compact PCB designs such as for a PD fast charger.

	DFN 8X8	DPAK
	- Matters OFHERE	San Contraction
L x W x H (mm ³)	8 x 8 x 0.85	9 x 6.5 x 2.2
Footprint (mm ²)	64	58.5
Volume(mm ³)	54	128
Rth (K/W) (For 6A SiC diode)	1.2	1.35





Table 2. WeEn SMD diode information

All information provided in this document is subject to legal disclaimers.

4. 120W PD charger design

4.1 Specification

This design uses a Critical Conduction Mode (CCM/DCM) PFC. It has AC mains input stage which converts AC mains to 400VDC (AC - 400 VDC), followed by an LLC DC-DC converter stage with input of 400V and output of 19.5VDC. For both stages, the switching frequency was increased to the maximum allowed by the control ICs that were readily available from "off-the-shelf". The PCB is designed as a demonstration board and is not yet optimized as a production design. Even so, with this design, a power density of 1.56 W/cc or 25.5 W/in³ was achieved, which is around 2x typical and 40% more than the best-in-class Si-based design available today. Customer designs are expected to achieve even higher power density.

The specification of the reference design is below:-

Term	Parameter	Value	Unit
V _{IN}	Input Voltage	90-264	V
		47-63	Hz
Vout	Output Voltage	19.5	V
Ιουτ	Output Current	6.2	A
Pout	Output Power	120	W
Fsw	PFC (115V, 100%load, CRM)	200	kHz
	PFC (230V, 100%load, DCM)	100	
	LLC	270	
η	Efficiency (230V, 100% load)	94.5	%
PF	Power Factor	0.95	

Table 3. PD charger reference design - specification

4.2 Semiconductor components

Function	Part Number	Quantity
PFC Diode	WNSC2D06650D	1
PFC FET	NV6115	2
PFC Controller	NCP1615CDR2G	1
LLC FET	NV6117	2
LLC Controller	NCP13992ABDR2G	1
SR MOS	NTMFS5C645NL	2
SR Controller	NCP4306AAAZZZAMNTWG	2

Table 4. PD charger reference design- semiconductor parts list

4.3 Schematic

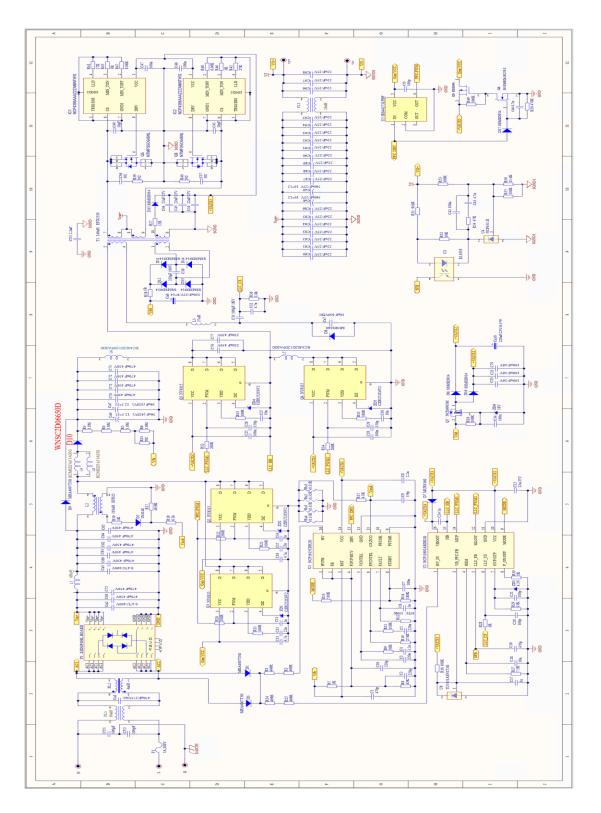


Fig. 6. PD charger reference design- schematic

WAN012

PD Charger (120W) Reference Design

4.4 PCB Board layout

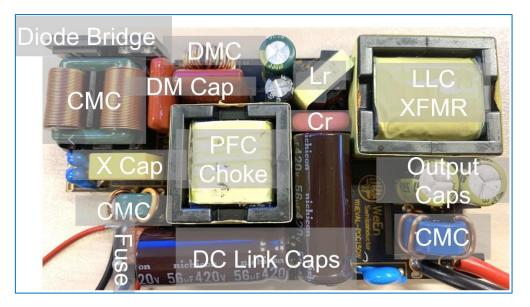


Fig. 7. PD charger reference design- PCB top view

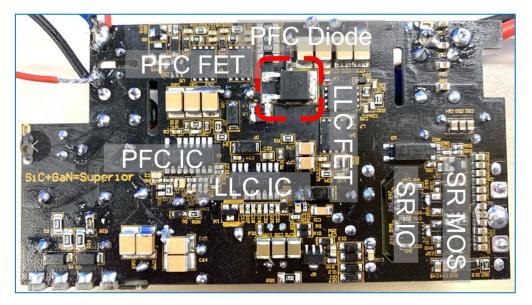


Fig. 8. PD charger reference design- PCB underside view

4.5 Connections and sequences

Start-up sequence:-

Set AC line to OVAC Set AC line to OFF Connect AC line input Connect DC load at the output Set AC line input to 120VAC Turn AC line input to ON Measure DC output voltage (19.5V) Increase output load current and monitor output voltage **Power-down sequence:** Turn-off AC power supply Turn-off the load

4.6 Switching waveforms

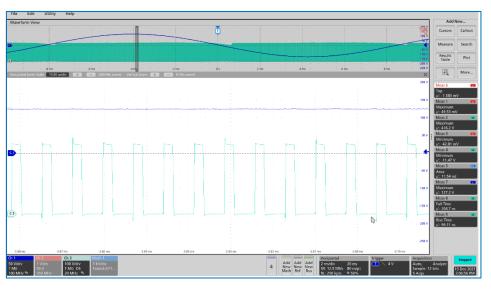


Fig. 9. CRM mode PFC Boost @ 90Vin, 400Vout, 120W, 140kHz

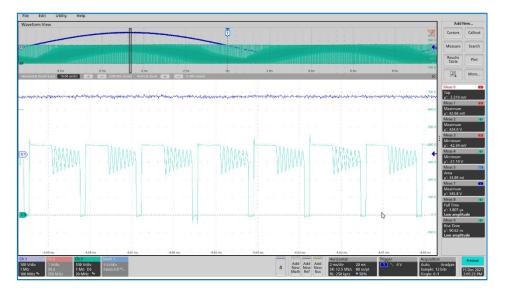


Fig. 10. DCM mode PFC Boost @ 230Vin, 400Vout, 120W, 110kHz

4.7 Efficiency curves and power factor curve

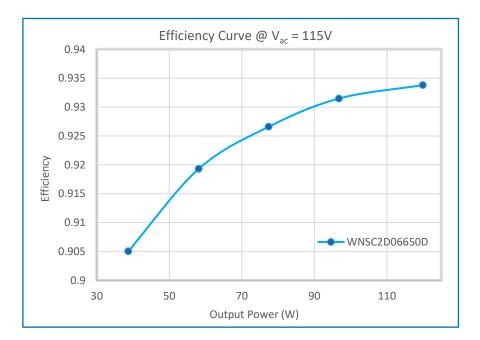


Fig. 11. Efficiency curve (115V)

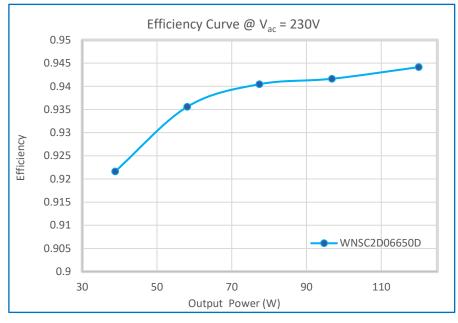


Fig. 12. Efficiency curve (230V)

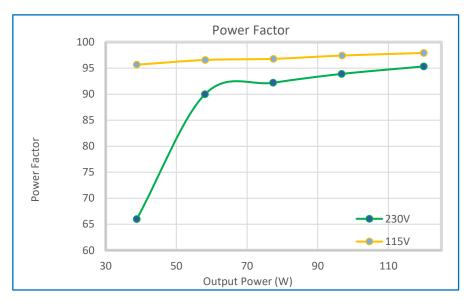


Fig. 13. Power factor curve

4.8 Thermal performance

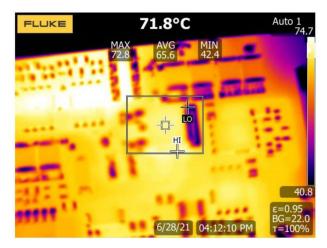


Fig. 14. WNSC2D06650D 71.8°C @ 90Vin, 120W full load, open frame and no cooling

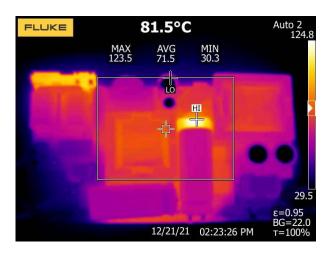


Fig. 15. PCB topside @ 90Vin, 120W full load, open frame and no cooling

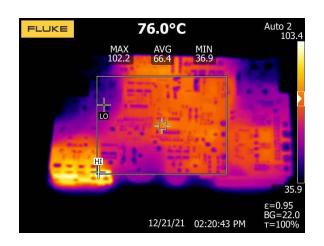


Fig. 16. PCB bottom @ 90Vin, 120W full load, open frame and no cooling

4.9 EMI measurement

Conducted EMI measurement results comply with EN55022 class B with 10dB margin. (See Figure 17)

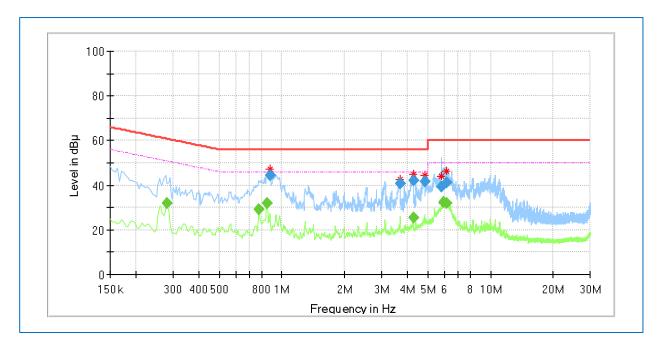


Fig. 17. Conducted EMI (Quasi-Peak blue, AVG green, V_{in} = 230V_{ac}, P_{out} = 120W)

Frequency (MHz)	QuasiPeak (dBµV)	Average (dBµV)	Limit (dBµV)	Margin (dB)
0.282000		31.87	50.76	18.89
0.774000		29.39	46.00	16.61
0.846000		32.03	46.00	13.97
0.878000	44.49		56.00	11.52
3.690000	40.63		56.00	15.37
4.254000	42.06		56.00	13.94
4.258000		25.66	46.00	20.34
4.826000	41.79		56.00	14.21
5.798000	39.27		60.00	20.73
5.942000		32.27	50.00	17.73
6.182000	41.38		60.00	18.62
6.186000		32.15	50.00	17.85

Revision history

Rev	Date	Description
v.01	20211223	New Application Note

Contact information

For more information or require engineering sample,

please visit: http://www.ween-semi.com_or contact our sales team representative haley.li@ween-semi.com

5. Legal information

Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. WeEn Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, WeEn Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. WeEn Semiconductors takes no responsibility for the content in this document if provided by an information source outside of WEEn Semiconductors.

In no event shall WeEn Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages

are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, WeEn Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of WeEn Semiconductors.

Right to make changes — WeEn Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — WeEn Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an WeEn Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. WeEn Semiconductors and its suppliers accept no liability for inclusion and/or use of WeEn Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. WeEn Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using WeEn Semiconductors products, and WeEn Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the WeEn Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third-party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

WeEn Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third-party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using WeEn

Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third-party customer(s). WeEn does not accept any liability in this respect.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Evaluation products — This product is provided on an "as is" and "with all faults" basis for evaluation purposes only. WeEn Semiconductors, its affiliates and their suppliers expressly disclaim all warranties, whether express, implied or statutory, including but not limited to the implied warranties of non-infringement, merchantability and fitness for a particular purpose. The entire risk as to the quality, or arising out of the use or performance, of this product remains with customer.

In no event shall WeEn Semiconductors, its affiliates or their suppliers be liable to customer for any special, indirect, consequential, punitive or incidental damages (including without limitation damages for loss of business, business interruption, loss of use, loss of data or information, and the like) arising out the use of or inability to use the product, whether or not based on tort (including negligence), strict liability, breach of contract, breach of warranty or any other theory, even if advised of the possibility of such damages.

Notwithstanding any damages that customer might incur for any reason whatsoever (including without limitation, all damages referenced above and all direct or general damages), the entire liability of WeEn Semiconductors, its affiliates and their suppliers and customer's exclusive remedy for all of the foregoing shall be limited to actual damages incurred by customer based on reasonable reliance up to the greater of the amount actually paid by customer for the product or five dollars (US\$5.00). The foregoing limitations, exclusions and disclaimers shall apply to the maximum extent permitted by applicable law, even if any remedy fails of its essential purpose.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

All information provided in this document is subject to legal disclaimers.

© WEEN 2021. All rights reserved.

6. Contents

1.	Introduction	1
2.	PD Charger using SiC diode	2
3.	WeEn SMD SiC diodes	4
4.	120W PD charger design	
4.1	Specification	5
4.2	Semiconductor components	6
4.3	Schematic	
4.4	PCB Board layout	8
4.5	Connections and sequences	
4.6	Switching waveforms	9
4.7	Efficiency curves and power factor curve	10
4.8	Thermal performance	12
4.9	EMI measurement	13
5.	Legal information	
Definit	tions	
Discla	imers	15
Trade	marks	15
6.	Contents	16

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information.

© WeEn 2021.

All rights reserved

For more information, please visit: <u>http://www.ween-semi.com</u> Date of release: 22 December 2021

Document identifier: WAN012